Abstracts

An Overload Protected Low-Noise X-Band FET Amplifier

E.C. Niehenke and T.E. Steigerwald. "An Overload Protected Low-Noise X-Band FET Amplifier." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 533-535.

Design and performance of a 40 dB gain X-band low-noise FET amplifier with integral overload protection is presented. Noise figures as low as 2 dB have been achieved using packaged transistors, including a multidiode overload protector that protects the FET's for input pulse powers to 1 kW. Performance is achieved by the use of new embedment circuits for super-low-noise packaged FET and pin diodes in aluminum-clad soft microstrip.

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